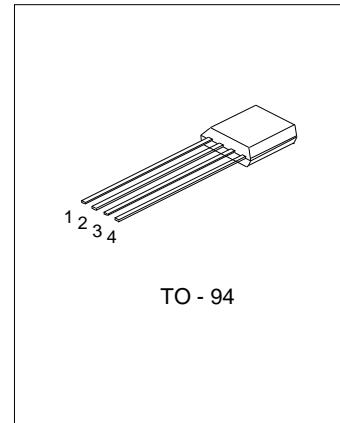


## BRUSH-LESS DC-FAN DRIVER WITH ON-CHIP HALL SENSOR

### DESCRIPTION

SA276 mainly designed for electronic commutation of brush-less DC fan. This IC internally includes the Hall Plate, Regulator, Pre-Amplifier, Comparator, and a pair of complementary open-collector Outputs (DO, DOB).

SA276 internally includes power-reverse protecting diode, the protecting diode only protects chips but not for coils. If necessary, add one external diode to block the reverse current from coils.



### FEATURES

- \* On-chip hall sensor
- \* Wide operating voltage: 3.5V to 20V
- \* 400mA (avg) output sink current
- \* Build-in power-reverse protecting diode only for reverse power connecting

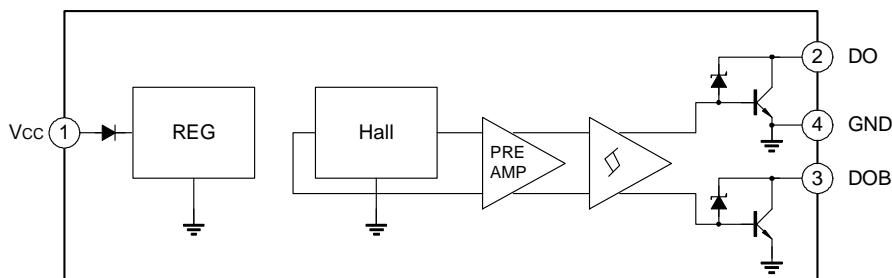
### ORDERING INFORMATION

Device	Package
SA276	TO-94

### APPLICATIONS

- \* Dual coils brush-less DC fan
- \* Dual coils brush-less DC motor
- \* Revolution counting
- \* Speed measurement

### BLOCK DIAGRAM



### ABSOLUTE MAXIMUM RATINGS ( $T_{amb}=25^{\circ}\text{C}$ )

Characteristics	Symbol	Value	Unit
Supply Voltage	Vcc	25	V
Reverse Vcc Polarity Voltage	Vrcc	-25	V
Magnetic Flux Density	B	Unlimited	G

(To be continued)

(Continued)

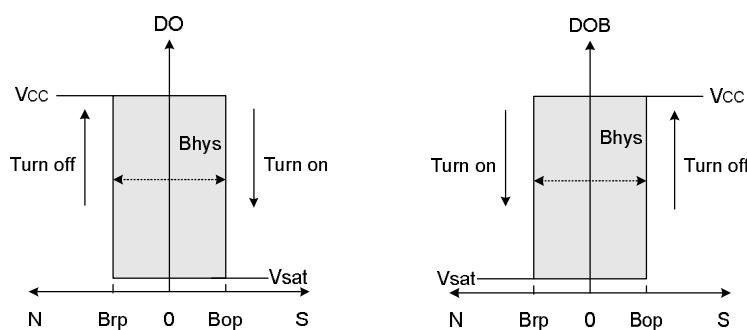
Characteristics		Symbol	Value	Unit
Output On Current	Continuous	I <sub>omax</sub>	400	mA
	Hold		500	mA
	Peak (start up)		700	mA
Maximum Junction Temp		T <sub>j</sub>	170	°C
Storage Temperature Range		T <sub>stg</sub>	-55~+150	°C
Operating Temperature Range		T <sub>tamb</sub>	-25~+85	°C
Package Power Dissipation( $T_{tamb} \leq 85^{\circ}\text{C}$ )		P <sub>tot</sub>	500	mW
Maximum Jointing Temp t≤10s		T <sub>sd</sub>	260	°C

**ELECTRICAL CHARACTERISTICS (T<sub>tamb</sub>=25°C, V<sub>cc</sub>=4.0V to 20V)**

Characteristics	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Supply Voltage	V <sub>cc</sub>		3.5		25	V
Supply Current	I <sub>cc</sub>	V <sub>CC</sub> =20V, R <sub>L</sub> =∞		16	25	mA
Low Supply Voltage	V <sub>ce</sub>	V <sub>CC</sub> =3.5V, I <sub>L</sub> =100mA		0.4		V
Output Saturation Voltage	V <sub>ce(sat)</sub>	V <sub>CC</sub> =12V, I <sub>L</sub> =300mA		0.3	0.5	V
Output Leakage Current	I <sub>cex</sub>	V <sub>CE</sub> =12V, V <sub>CC</sub> =12V		<0.1	10	μA
Output Rise Time	t <sub>r</sub>	V <sub>CC</sub> =12V, R <sub>L</sub> =820Ω, C <sub>L</sub> =20pF		3.0	10	μs
Output Falling Time	t <sub>f</sub>	V <sub>CC</sub> =12V, R <sub>L</sub> =820Ω, C <sub>L</sub> =20pF		0.4	2	μs
Switch Time Differential	Δt	V <sub>CC</sub> =14V, R <sub>L</sub> =820Ω, C <sub>L</sub> =20pF		3.0	10	μs
Output Zener Breakdown	V <sub>z</sub>			40		V

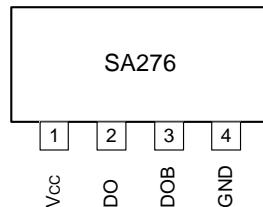
**MAGNETIC CHARACTERISTICS**

Characteristics	Symbol	Test circuit	Min.	Typ.	Max.	Unit
Operate Point	B <sub>op</sub>	T <sub>tamb</sub> =25°C	0	--	70	G
		T <sub>tamb</sub> =-25~+85°C	0	--	70	G
Release Point	B <sub>rp</sub>	T <sub>tamb</sub> =25°C	0	--	-70	G
		T <sub>tamb</sub> =-25~+85°C	0	--	-70	G
Hysteresis	B <sub>phys</sub>	T <sub>tamb</sub> =25°C	20	--	140	G
		T <sub>tamb</sub> =-25~+85°C	10	--	140	G



While the magnetic flux density B is larger than operate point B<sub>op</sub>, DO will turn on and output low potential, DOB will turn off and output high potential. Each output is latched until the magnetic flux density B is lower than release point B<sub>rp</sub>, and then DO; DOB transfer each state.

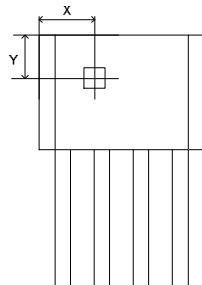
### PIN CONFIGURATION



### PIN DESCRIPTION

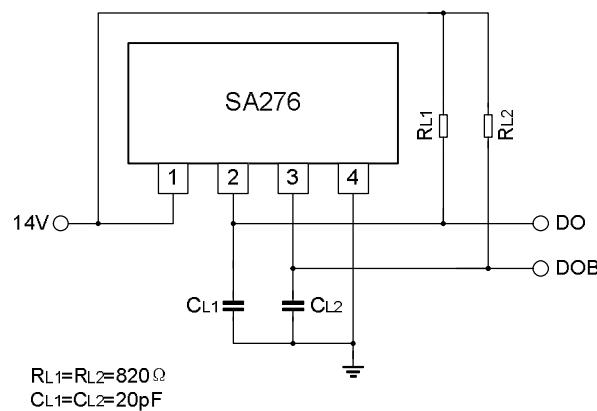
Pin No.	Symbol	Description
1	Vcc	Power supply
2	DO	Positive output
3	DOB	Negative output
4	GND	Ground.

### HALL SENSOR LOCATION

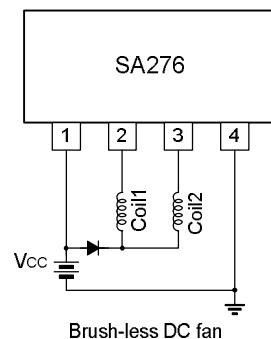


		Unit
X	1.75	mm
Y	1.35	mm

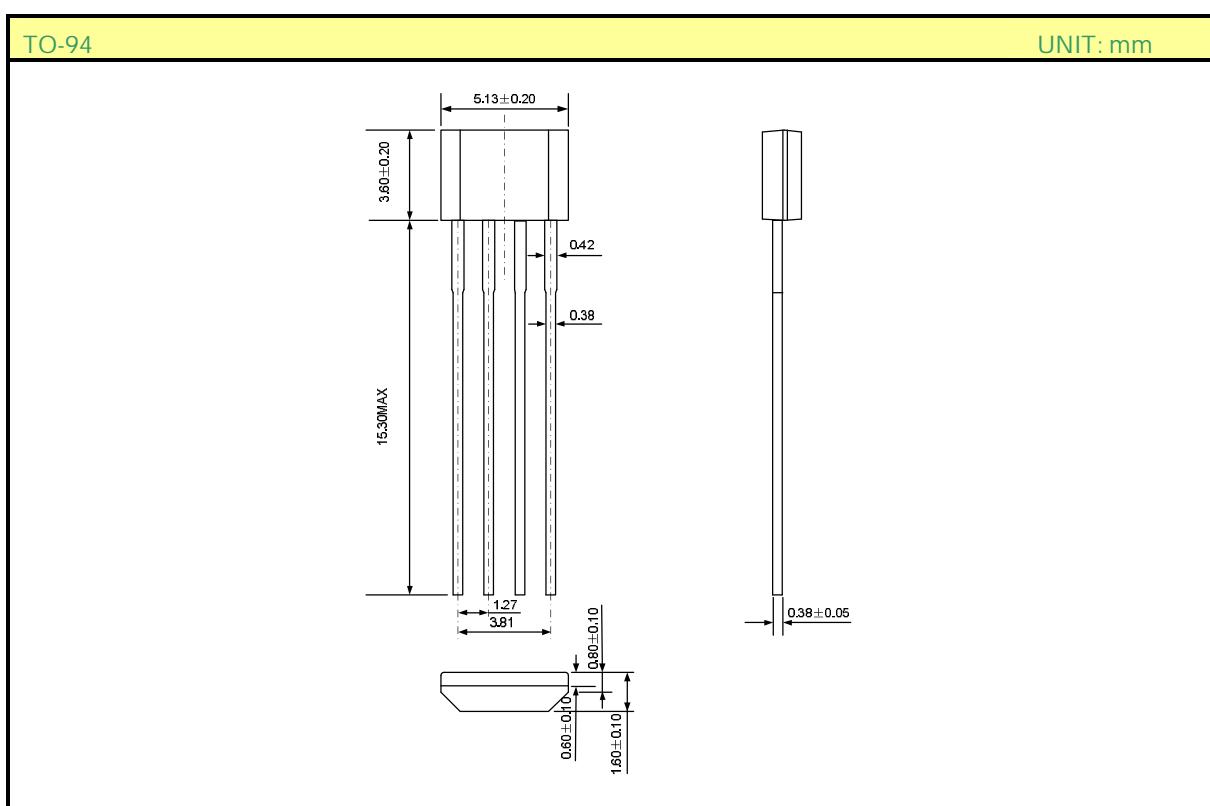
### TEST CIRCUIT



TYPICAL APPLICATION CIRCUIT



PACKAGE OUTLINE



ATTACH

## Revision History

Data	REV	Description	Page
2004.06.28	1.0	Original	
2004.07.15	1.1	Modify the "PACKAGE OUTLINE".	5